

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$ $T_A = 25^\circ C$
-100V	350m $\Omega$ @ $V_{GS} = -10V$	-3.9A
	450m $\Omega$ @ $V_{GS} = -6.0V$	-3.4A

## Description and Applications

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- DC-DC Converters
- Power management functions
- Uninterrupted power supply

## Features and Benefits

- Fast switching speed
- Low gate drive
- Low input capacitance
- **Qualified to AEC-Q101 Standards for High Reliability**

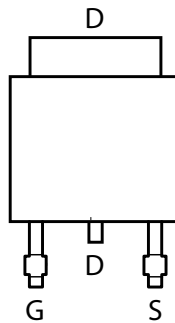
## Mechanical Data

- Case: TO252-3L
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.33 grams (approximate)

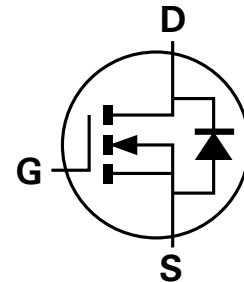
TO252-3L



Top View



Pin Out – Top View

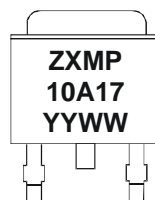


Equivalent Circuit

## Ordering Information

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMP10A17KTC	See below	13	16	2,500

## Marking Information



ZXMP = Product Type Marking Code, Line 1  
 10A17 = Product Type Marking Code, Line 2  
 YYWW = Date Code Marking  
 YY = Year (ex: 09 = 2009)  
 WW = Week (01-52)

**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

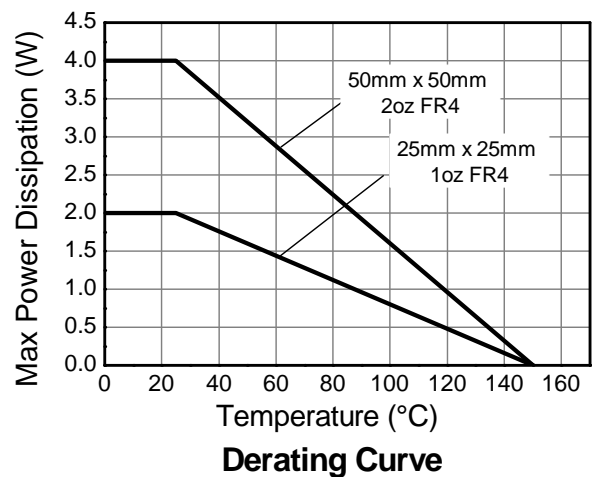
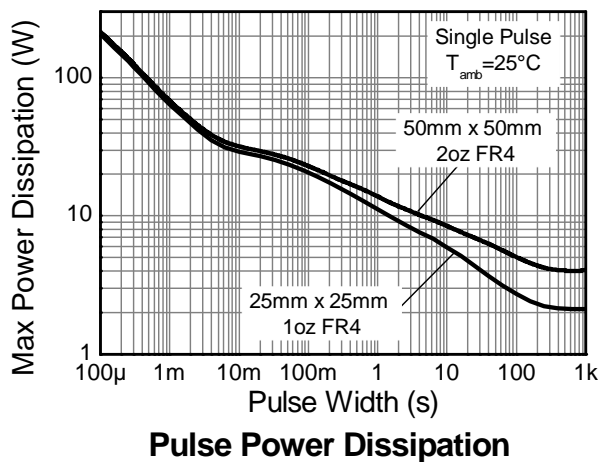
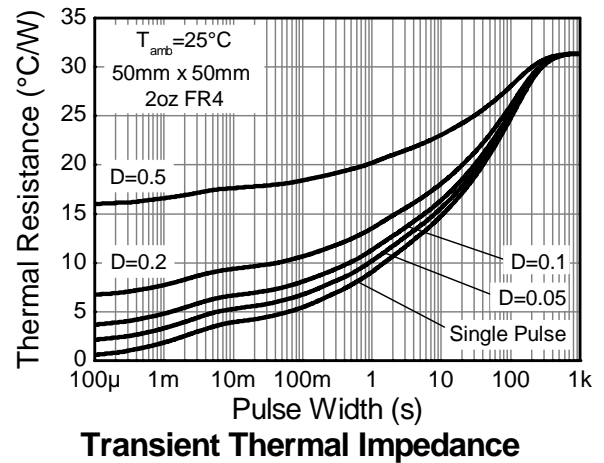
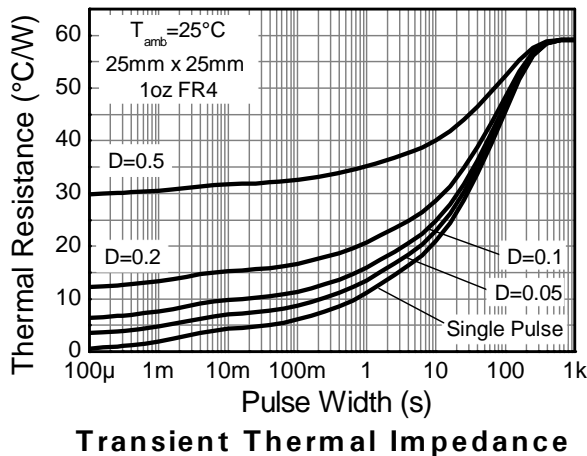
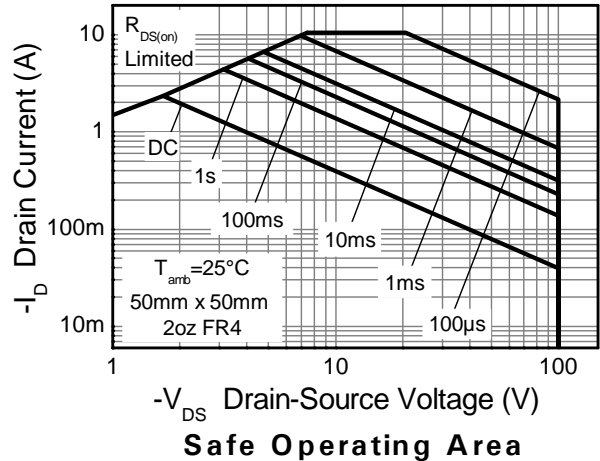
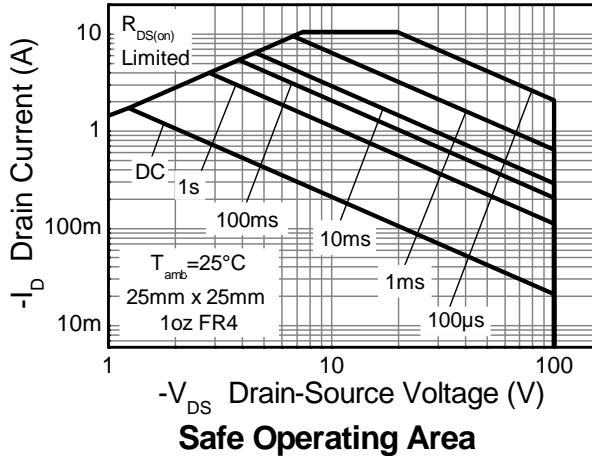
Characteristic			Symbol	Value	Unit
Drain-Source voltage			V <sub>DSS</sub>	-100	V
Gate-Source voltage			V <sub>GS</sub>	±20	V
Continuous Drain current	V <sub>GS</sub> = 10V	(Note 2)	I <sub>D</sub>	-3.9	A
		T <sub>A</sub> = 70°C (Note 2)		-3.1	
		(Note 1)		-2.4	
Pulsed Drain current	V <sub>GS</sub> = 10V	(Note 3)	I <sub>DM</sub>	-11.3	A
Continuous Source current (Body diode)			I <sub>S</sub>	-8.7	A
Pulsed Source current (Body diode)			I <sub>SM</sub>	-11.3	A

**Thermal Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Power dissipation Linear derating factor		(Note 1)	P <sub>D</sub>	4.0	W mW/°C
				32.0	
		(Note 2)		10.2	
				80.8	
		(Note 5)		2.0	
Thermal Resistance, Junction to Ambient		(Note 1)	R <sub>θJA</sub>	31	°C/W
		(Note 2)		12.3	
		(Note 5)		62	
Thermal Resistance, Junction to Case		(Note 4)	R <sub>θJL</sub>	2.4	°C/W
Operating and storage temperature range			T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

- Notes:
1. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  2. Same as note (1), except the device is measured at t ≤ 10 sec.
  3. Same as note (1), except the device is pulsed with D= 0.02 and pulse width 300 μs. The pulse current is limited by the maximum junction temperature.
  4. Thermal resistance from junction to solder-point (at the end of the drain lead).
  5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

**Thermal Characteristics**

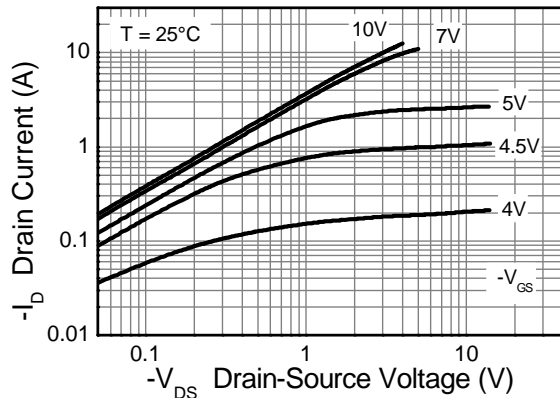


**Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

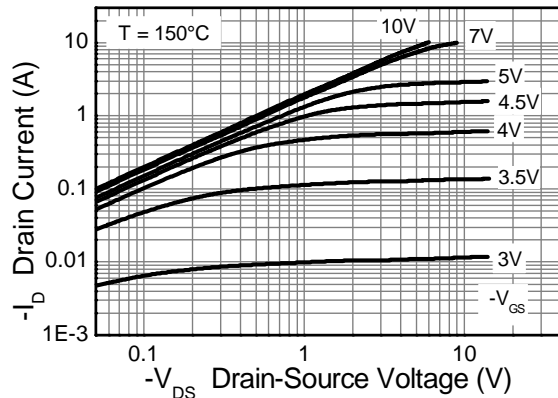
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-100	—	—	V	I <sub>D</sub> = -250μA, V <sub>GS</sub> = 0V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-0.5	μA	V <sub>DS</sub> = -100V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-2.0	—	-4.0	V	I <sub>D</sub> = -250μA, V <sub>DS</sub> = V <sub>GS</sub>
Static Drain-Source On-Resistance (Note 6)	R <sub>DS(on)</sub>	—	—	0.350	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -1.4A
				0.450		V <sub>GS</sub> = -6V, I <sub>D</sub> = -1.2A
Forward Transconductance (Notes 6 & 7)	g <sub>fs</sub>	—	2.8	—	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -1.4A
Diode Forward Voltage (Note 6)	V <sub>SD</sub>	—	-0.85	-0.95	V	I <sub>S</sub> = -1.7A, V <sub>GS</sub> = 0V
Reverse recovery time (Note 7)	t <sub>rr</sub>	—	33	—	ns	I <sub>S</sub> = -1.5A, di/dt = 100A/μs
Reverse recovery charge (Note 7)	Q <sub>rr</sub>	—	48	—	nC	
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	424	—	pF	V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	36.6	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	29.8	—	pF	
Total Gate Charge (Note 8)	Q <sub>g</sub>	—	7.1	—	nC	V <sub>GS</sub> = -6.0V
Total Gate Charge (Note 8)	Q <sub>g</sub>	—	10.7	—	nC	V <sub>GS</sub> = -10V
Gate-Source Charge (Note 8)	Q <sub>gs</sub>	—	1.7	—	nC	
Gate-Drain Charge (Note 8)	Q <sub>gd</sub>	—	3.8	—	nC	
Turn-On Delay Time (Note 8)	t <sub>D(on)</sub>	—	3.0	—	ns	V <sub>DD</sub> = -50V, V <sub>GS</sub> = -10V I <sub>D</sub> = -1A, R <sub>G</sub> ≅ 6.0Ω
Turn-On Rise Time (Note 8)	t <sub>r</sub>	—	3.5	—	ns	
Turn-Off Delay Time (Note 8)	t <sub>D(off)</sub>	—	13.4	—	ns	
Turn-Off Fall Time (Note 8)	t <sub>f</sub>	—	7.2	—	ns	

- Notes:
6. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
  7. For design aid only, not subject to production testing.
  8. Switching characteristics are independent of operating junction temperatures.

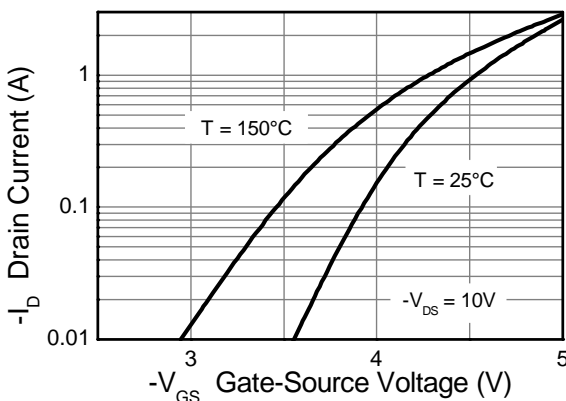
**Typical Characteristics**



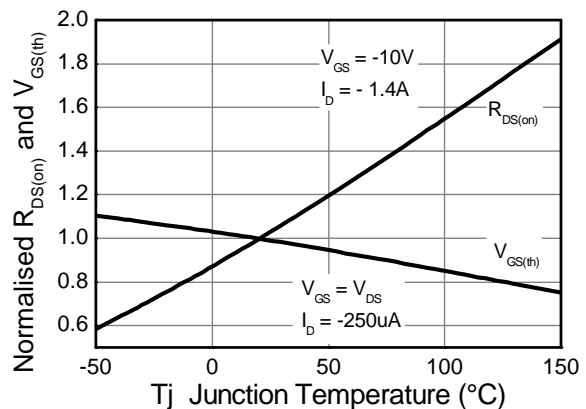
**Output Characteristics**



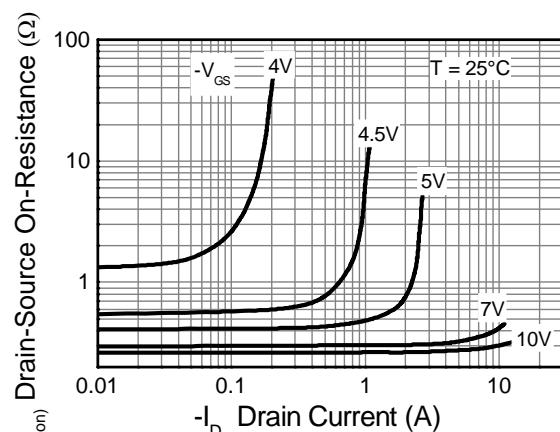
**Output Characteristics**



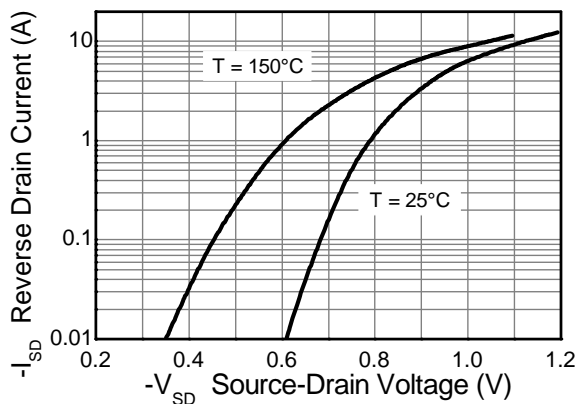
**Typical Transfer Characteristics**



**Normalised Curves v Temperature**

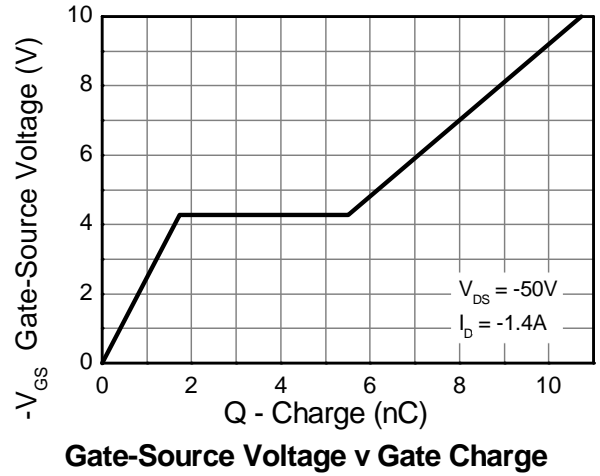
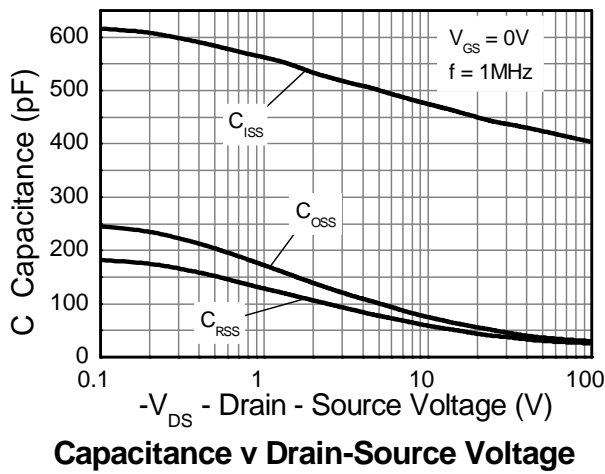


**On-Resistance v Drain Current**

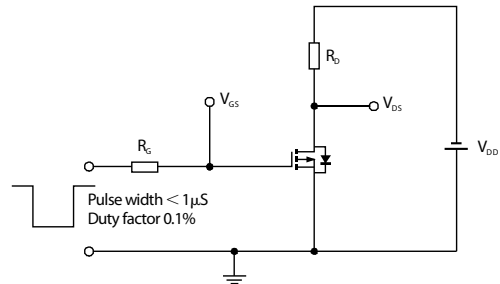
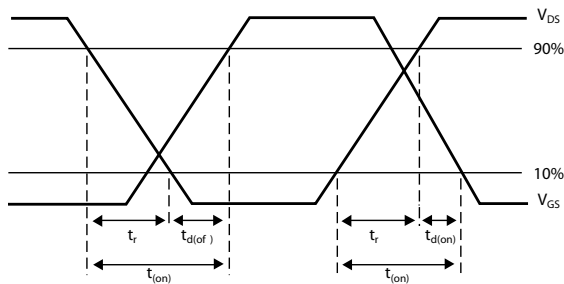
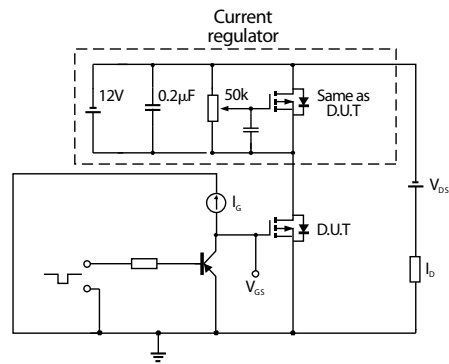
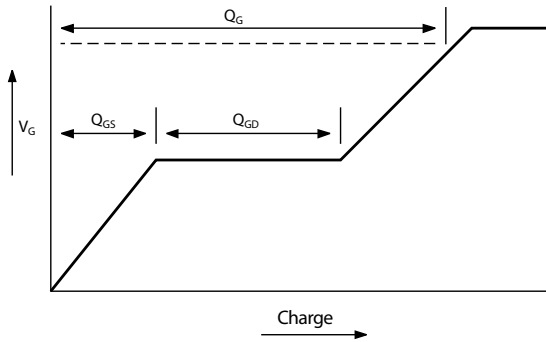


**Source-Drain Diode Forward Voltage**

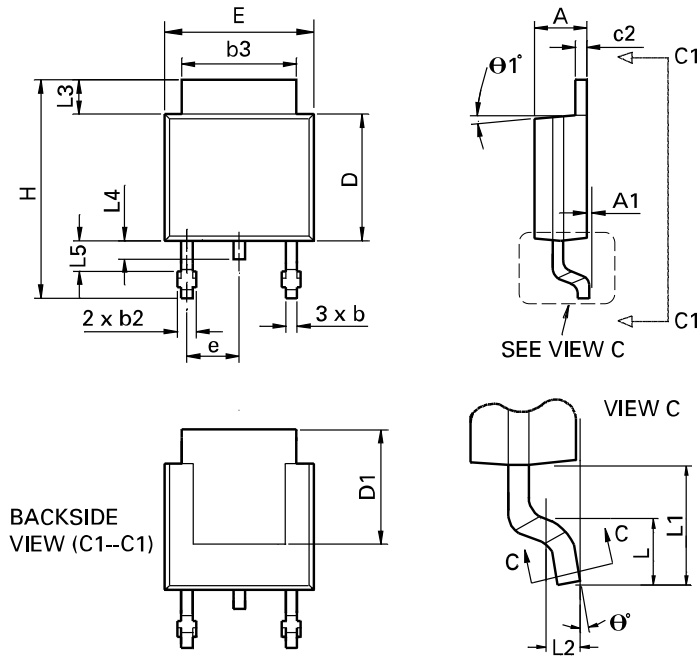
**Typical Characteristics - continued**



**Test Circuits**

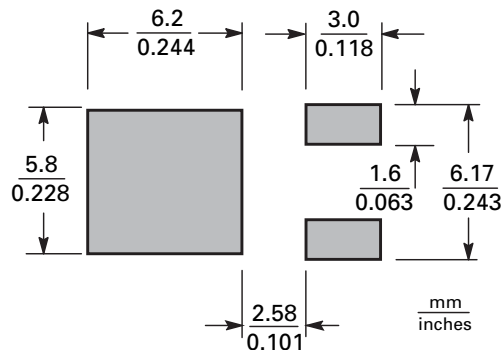


**Package Outline Dimensions**



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.086	0.094	2.18	2.39	e	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	H	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	$\theta_1^\circ$	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	$\theta^\circ$	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

**Suggested Pad Layout**



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